High Speed Performance of Electrooptic Polymer Modulator Devices in Advanced Optical Communication Systems

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Abstract- Electrooptic polymer modulator devices have been extensively studied and explored during the last few years. They have intrinsic advantages over conventional materials such as high-speed operation, compatibility with other materials and substrates, and the ability to make complex configurations and arrays. On the other hand, there have been problems with thermal stability, power handling, and drift. These problems are currently the subject of intense research and must be solved before commercial devices become available. This paper has been deeply investigated the high speed performance of polymer electrooptic modulator devices in advanced optical communication systems over wide range of the affecting parameters. We have taken in to account the study of modulator signal quality, sensitivity bandwidth product, switching voltage, transmitted signal bandwidth, device sensitivity, transmission bit rates under the effect of operating optical signal wavelength, modulator dimensions (i. e, modulator length, width and thickness), ambient temperature, and effective relative refractive index difference as a measurement of high speed performance operation.

Index Terms— Optical Polymers, Integrated Optics Devices, High Speed Performance, Communication Systems and Modulator Sensitivity

I. INTRODCTION

THE development of low loss, highly linear, and lowdispersion optical links coupled with the linear response of optical detectors to the intensity of incident light stream would make optical links an attractive alternative to microwave/millimeter links. Important applications include: 1) satellite receiver systems for distributed RF signals over long distances with high signal quality; 2) remote antenna and active phased array by means of high quality, low loss RF photonics without complicated digital processing equipment; and 3) local area networks (LANs) for low distortion distribution of RF signals in large building complexes, aircrafts, and television network systems [1, 2]. In these fields, highly efficient and linearized conversion from RF carrier based signals to optical carrierbased signals is of paramount importance.

A substantial research work performed over the past years has resulted in a number of linearization techniques, which can be subdivided into two categories, namely, electronic compensation and optical techniques of linearization. Electronic compensation includes pre-distortion compensation [3] and feed forward compensation [4]. Yet these techniques require expensive high-speed optoelectronic components, and have maximum bandwidth of only a few gigahertz. Optical techniques based on cascaded Mach Zehnder (MZ) modulator [5], dual wavelength MZ modulation [6], or ring resonator assisted MZ modulator [7] can achieve high bandwidth linearization, however, with a common shortcoming of complex device structure. In addition, these complex devices require high thermal stability and precise bias voltage, which substantially limit its use in practical applications [8].

In the present study, we have deeply investigated electrooptic polymer modulator device to estimate rise time, transmitted signal bandwidth, transmitted data rats and transmission bit rate length product, and switching voltage with using pulse code modulation scheme. The reliability of high speed electrooptic polymer modulators is the most critical milestone for the use of these materials in commercial applications.

II. MODEL ANALYSIS

The effective refractive index, n_e of polymer material based electrooptic modulator device can be given as [9]:

$$n_e^2 = \frac{B_1 \lambda^2}{\lambda^2 - B_2^2} + \frac{B_3 \lambda^2}{\lambda^2 - B_4^2} + \frac{B_5 \lambda^2}{\lambda^2 - B_6^2} \quad , \tag{1}$$

The set of parameters of empirical equation coefficients of polymer material are recast as the following: $B_1=0.4963$, $B_2=0.0718(T/T_0)^2$, $B_3=0.6965$, $B_4=0.1174$ $(T/T_0)^2$, $B_5=0.3223$, and $B_6=9.237$ $(T/T_0)^2$. Where T is the ambient temperature, and T_0 is the room temperature. Then the first and second differentiation of empirical equation with respect to operating wavelength λ yields as mentioned in Ref. [10]. The switching voltage V_{π} or the voltage required to change the output light intensity from its maximum value to its minimum value can be expressed as the following [11]:

$$V_{\pi} = \frac{\lambda d}{2\Gamma n_e^3 r_{33} L_m} , \qquad (2)$$

Where d is the modulator thickness, λ is the operating optical signal wavelength, Γ is the confinement factor, L_m is the modulator length, and r_{33} is the electrooptic coefficient. If a modulating voltage V_m in z-direction is applied, the change in index for the transverse magnetic (TM) polarization is:

$$\Delta n_e = \frac{0.5 V_m \, n_e^3 \, r_{33}}{L_m} \, , \tag{3}$$

The sensitivity (S) of the EO polymer modulator can be written as [12]:

$$S = \frac{0.65 \ Q \Gamma \, r_{33} \, n_e^2}{d} \quad , \tag{4}$$

Where Q is the quality factor of the EO polymer modulator device. The higher Q device will have higher sensitivity, as expected. The bandwidth of the modulator is inversely proportional to the Q. However, the product of the sensitivity and the bandwidth is not related to the Q and is given by [13-15]:

$$SBP = \frac{0.65 n_e^2 \Gamma r_{33} c}{d \lambda} \quad , \tag{5}$$

The quality factor of the EO polymer modulator device Q can be expressed as the following [16, 17]:

$$Q = \sqrt{m_1} - \sqrt{m_0} \quad , \tag{6}$$

Where $m_0=m_{b0}+m_d$ is the average number of electrons representing the 'zero' symbol, $m_1=m_{b1}+m_d$ is the average number of electrons representing the 'one' symbol, $m_d=i_d$ T_s/q is the average number of electrons correspond the dark current i_d during the switching time T_s . Where $m_{b0}=\lambda\eta P_0T_s/hc$, $m_{b1}=\lambda\eta P_1T_s/hc$. Where η is the efficiency of EO polymer modulator device, h is the Plank's constant (6.625x10⁻³⁴ J.Sec), q is the electron charge (1.602x10⁻¹⁹ C), P_0 is the optical power representing the 'zero' symbol, and P_1 is the optical power representing the 'one' symbol. The transmitted signal bandwidth for standard single mode for polymer material based electrooptic modulator length L_m is given by [18]:

$$BW_{sig.} = \frac{0.44}{\Delta \tau \cdot L_m} , \qquad (7)$$

Where $\Delta \tau$ is the total pulse broadening due to total dispersion coefficient in system based EO modulator:

$$\Delta \tau = D_t \,\Delta \lambda \, L_m \quad , \ n \, \text{sec} / \, nm.cm \tag{8}$$

Where the total dispersion coefficient in system based EO modulator device is given by:

$$D_t = \left(M_{md} + P\right) \quad , \tag{9}$$

In which both material and profile dispersions were taken into account as M_{md} and P respectively [19, 10]:

$$M_{md} = \left(-\frac{\lambda^3}{c} \left(\frac{dn_e}{d\lambda}\right)^2 - \frac{2\lambda}{c} \left(\frac{d^2n_e}{d\lambda^2}\right) (N_1 \Delta n_e) C_1 \left(\frac{2\alpha}{\alpha+2}\right)^{0.5}$$
(10)

$$P = \left[\left(\frac{N_1 \Delta n_e}{c\lambda} \right)^2 \left(\frac{\alpha - 2 - \varepsilon}{\alpha + 2} \right)^2 \times \frac{2\alpha}{3\alpha + 2} \right]^{\frac{1}{2}}$$
(11)

Where N_1 is the group index for the mode which is given by:

$$N_1 = n_e - \lambda \frac{dn_e}{d\lambda} \quad , \tag{12}$$

Where C_1 is a constant related to index exponent and profile dispersion and is given by:

$$C_1 = \frac{\alpha - 2 - \varepsilon}{\alpha + 2} \quad , \tag{13}$$

Where α is the index exponent, and ε is the profile dispersion parameter, and is given by:

$$r = -\frac{2n_e}{N_1} \frac{\lambda}{\Delta n_e} \quad , \tag{14}$$

In the pulse code modulation scheme, total transmitted bit rate within EO polymer modulator device can be expressed in terms of transmitted signal bandwidth, and number of quantization levels, M as the following formula [20]:

$$R_T(PCM) = 2 B.W_{sig.} \log_2 M \quad , \tag{15}$$

III. SIMULATION RESULTS AND DISCUSSIONS

We have been investigated the high speed performance operation of electrooptic polymer modulator in high speed optical communication over wide range of the affecting operating parameters as shown listed as follows: 1.3 μ m $\leq \lambda$, optical signal wavelength $\leq 1.55 \ \mu m$, Spectral line width of the optical source, $\Delta \lambda = 0.1$ nm, 300 K \leq T, ambient temperature \leq 330 K, room temperature, T₀=300 K, 0.2 μ m \leq L_m, modulator length \leq 1 µm, speed of light, c=3 x10¹⁰ cm/sec, 0.5 msec \leq switching time, T_s (on state) \leq 1 msec, 0.1 msec \leq switching time, T_s (off state) \leq 0.4 msec, 0.1 μ A \leq dark current, $i_d \leq 1 \mu A$, electro-optic coefficient, $r_{33}=300$ pm/Volt, $0.8 \leq$ confinement factor, $\Gamma \leq 0.95$, $0.01 \leq$ relative refractive index difference, $\Delta n_e \leq 0.05$, 0.1 Watt \leq optical power, $P_0=P_1 \leq 0.6$ Watt, quantum Efficiency, $\eta=90$ %, index exponent, $\alpha=2$, $16 \leq$ number of quantization levels, M $\leq 128.$

Based on the model equations analysis, assumed set of the operating parameters, and the set of the Figs. (1-12), the following facts are assured as the following results:

- i) As shown in Figs. (1, 2) have assured that as both modulator length and ambient temperature increase, this results in decreasing of both transmitted signal bandwidth and transmission bit rate.
- Figs. (3, 4) have demonstrated that as both ambient temperature and operation optical signal wavelength increase, this leads to decrease in both transmitted signal bandwidth and transmission bit rate.
- iii) As shown in Figs. (5, 6) have indicated that as both relative refractive index difference and operation optical signal wavelength increase, this leads to decrease in both transmitted signal bandwidth and transmission bit rate.
- iv) Fig. 7 has assured that as number of quantization levels increases and operating optical signal wavelength deceases, these results in increasing of transmission bit rate.
- v) Figs. (8, 9) have indicated that as modulator length increases, and both relative refractive index difference and operating signal wavelength increase, this leads to increase in both modulating and switching voltages.
- vi) Fig. 10 has demonstrated that as optical signal wavelength decreases and dark current increases, these results in decreasing of modulator signal quality factor.
- vii) As shown in Fig. 11 has indicated that as confinement factor increases, and modulator thickness decreases, these results in increasing of modulator device sensitivity.



Fig. 1. Variations of signal bandwidth against ambient temperature at the assumed set of parameters.



Fig. 2. Variations of the transmission bit rate against modulator length at the assumed set of parameters.



Fig. 3. Variations of transmitted signal bandwidth against optical signal wavelength at the assumed set of parameters.



Fig. 4. Variations of transmission bit rate against optical signal wavelength at the assumed set of parameters.



Fig. 5. Variations of transmitted signal bandwidth against optical signal wavelength at the assumed set of parameters.



Optical signal wavelength, λ , μ m

Fig. 6. Variations of transmission bit rate against optical signal wavelength at the assumed set of parameters.



Fig. 7. Variations of transmission bit rate against number of quantization levels at the assumed set of parameters.



Fig. 8. Variations of switching voltage against optical signal wavelength at the assumed set of parameters.



Fig. 9. Variations of modulator voltage against relative refractive index difference at the assumed set of parameters.







Confinement factor, Γ

Fig. 11. Variations of polymer modulator sensitivity versus confinement factor at the assumed set of parameters.



Modulator thickness, d, µm

Fig. 12. Variations of sensitivity bandwidth product against modulator thickness at the assumed set of parameters.

viii) Fig. 12 has assured that as modulator thickness increases and confinement factor decreases, this leads to decrease in modulator sensitivity bandwidth product.

IV. CONCLUSIONS

In a summary, this paper has presented the high speed performance of electrooptic polymer modulator devices in advanced optical communication systems. The transmitted signal bandwidth, modulator signal quality factor, transmission bit rate, switching and modulating voltages, modulator sensitivity and sensitivity bandwidth product have been investigated over wide range of the affecting parameters as the good criteria of the high speed performance for fast operation. It is theoretically found that the increased operating optical signal wavelength, ambient temperature, modulator length, and relative refractive index difference, this results in the decreased of transmitted signal bandwidth, and transmission bit rates, and the increased switching and modulating voltages. It is also evident that the increased confinement factor and the decreased modulator thickness, this leads to the increased modulator sensitivity. As well as the increased modulator thickness and the decreased confinement, this results in the decreased modulator sensitivity bandwidth product.

REFERENCES

- J. Macario, P. Yao, R. Shireen, C. A. Schuetz, S. Y. Shi, and D. W. Prather, "Development of Electro-optic Phase Modulator for 94 GHz Imaging System," Journal of Lightwave Technology, Vol. 27, No. 6, pp. 5698–5703, 2009.
- [2] Abd El-Naser A. Mohammed, Mohamed M. E. El-Halawany, Ahmed Nabih Zaki Rashed, and Mohammed S. F. Tabour "High Transmission Performance of Radio over Fiber Systems over Traditional Optical Fiber Communication Systems Using Different Coding Formats for Long Haul" International Journal of Computer Science and Telecommunications (IJCST), Vol. 2, No. 3, pp. 29-42, June 2011.
- [3] Abd El-Naser A. Mohammed, Nabil Ayad, Ahmed Nabih Zaki Rashed, and Hazem M. Hageen "Speed Response and Performance Degradation of High Temperature Gamma Irradiated Silicon PIN Photodiodes" International Journal of Computer Science and Information Security (IJCSIS), Vol. 9, No. 5, pp. 268-275, May 2011.
- [4] Y. Liao, H. Zhou, and Z. Meng, "Modulation Efficiency of a LiNbO₃ Waveguide Electro-optic Intensity Modulator Operating at High Microwave Frequency," Optics Letters, Vol. 34, No. 12, pp. 1822–1824, 2009.
- [5] Abd El-Naser A. Mohammed, Gaber E. S. M. El-Abyad, Abd El-Fattah A. Saad, and Ahmed Nabih Zaki Rashed, "High Transmission Bit Rate of A thermal Arrayed Waveguide Grating (AWG) Module in Passive Optical Networks," IJCSIS International Journal of Computer Science and Information Security, Vol. 1, No. 1, pp. 13-22, May 2009.
- [6] Q. Y. Lu, W. H. Guo, D. Byrne, and J. F. Donegan, "Design of Low V_{-pi} High Speed GaAs Traveling Wave Electrooptic Phase Modulators Using an n-i-p-n Structure," IEEE Photonics Technology Letters, Vol. 20, No. 3, pp. 1805–1807, 2008.
- [7] Abd El-Naser A. Mohammed, Mohamed A. metawe'e, Ahmed Nabih Zaki Rashed, and Amina E. M. El-Nabawy "Unguided Nonlinear Optical Laser Pulses Propagate in Waters With Soliton Transmission Technique" International Journal of Multidisciplinary Sciences and Engineering (IJMSE), Vol. 2, No. 1, pp. 1-10, March 2011.
- [8] M. Jarrahi, T. H. Lee, and D. A.B. Miller, "Wideband, Low Driving Voltage Traveling Wave Mach-Zehnder Modulator for RF Photonics," IEEE Photonics Technology Letters, Vol. 20, No. 7, pp. 517–519, 2008.
- [9] Abd El-Naser A. Mohammed, Mohamed M. E. El-Halawany, Ahmed Nabih Zaki Rashed, and Sakr Hanafy "High Performance of Plastic Optical Fibers within Conventional Amplification Technique in Advanced Local Area Optical Communication Networks " International Journal of Multidisciplinary Sciences and Engineering (IJMSE), Vol. 2, No. 2, pp. 34-42, May 2011.

- [10] Abd El-Naser A. Mohammed, Mohamed M. E. El-Halawany, Ahmed Nabih Zaki Rashed, and Mohamoud M. Eid "Optical Add Drop Multiplexers with UW-DWDM Technique in Metro Optical Access Communication Networks" International Journal of Computer Science and Telecommunications (IJCST), Vol. 2, No. 2, pp. 5-13, April 2011.
- [11] Abd El-Naser A. Mohammed, Abd El-Fattah A. Saad, and Ahmed Nabih Zaki Rashed, "Study of the Thermal and Spectral Sensitivities of Organic-Inorganic Fabrication Materials Based Arrayed Waveguide Grating for Passive Optical Network Applications," Journal of Engineering and Technology Research, Vol. 1, No. 5, pp. 81-90, Aug. 2009.
- [12] T. Gorman, S. Haxha, and J. J. Ju, "Ultra High Speed Deeply Etched Electrooptic Polymer Modulator With Profiled Cross Section," Journal of Lightwave Technology, Vol. 27, No. 1, pp. 68–76, 2009.
- [13] L.R.Dalton, P. A. Sullivan, and D. H. Bale, "Electric Field Poled Organic Electro-optic Materials: State of the Art and Future Prospects," Chemical Reviews, Vol. 110, No. 1, pp. 25–55, 2010.
- [14] J.-M. Brosi, C. Koos, L. C. Andreani, M. Waldow, J. Leuthold, and W. Freude, "High Speed Low Voltage Electrooptic Modulator With a polymer Infiltrated Silicon Photonic Crystal Waveguide," Optics Express, Vol. 16, No. 6, pp. 4177–4191, 2008.
- [15] S. Shi and D. W. Prather, "Dual Optical Slot Waveguide for Ultra Broadband Modulation With A sub Volt V_p," Applied Physics Letters, Vol. 96, No. 3, pp. 201-212, 2010.
- [16] Abd El-Naser A. Mohammed, Abd El-Fattah A. Saad, and Ahmed Nabih Zaki Rashed, "Applications of Arrayed Waveguide Grating (AWG) in Passive Optical Networks," IJFGCN International Journal of Future Generation Communication and Networking, Vol. 2, No. 2, pp. 25-36, June 2009.
- [17] E. W. Taylor, J. E. Nichter, F. D. Nash, F. Haas, A. A. Szep, R. J. Michalak, B. M. Flusche, P. R. Cook, T. A. McEwen, B. F. McKeon, P. M. Payson, G. A. Brost, A. Pirich, C. Castenada, B. Tsap, and H. R. Fetterman, "Radiation Resistance of Electro-optic Polymer Based Modulators," Appl. Phys. Lett., Vol. 86, No. 3, pp. 201122-1–201122-3, 2005.
- [18] Abd El-Naser A. Mohammed, Ahmed Nabih Zaki Rashed, and Mohammed S. F. Tabour, "Transmission Characteristics of Radio over Fiber (ROF) Millimeter Wave Systems in Local Area Optical Communication Networks" International Journal of Advanced Networks and Applications, Vol. 2, No. 6, pp. 876-886, May/June 2011.
- [19] Abd El-Naser A. Mohammed, Abd El-Fattah A. Saad, and Ahmed Nabih Zaki Rashed, "Characteristics of the Fabrication Materials Based Arrayed Waveguide Grating (AWG) in Passive Optical Networks (PONs)," International Journal of Material Sciences Research, Vol. 1, No. 6, pp. 89-97, June 2009.
- [20] P. S. Devgan, J. F. Diehl, V. J. Urick, C. E. Sunderman, and K. J. Williams, "Even Order Harmonic Cancellation for Off Quadrature Biased Mach-Zenhder Modulator With Improved RF Metrics Using Dual Wavelength Inputs and Dual Outputs," Opt. Exp., Vol. 17, No. 2, pp. 9028–9039, 2009.